Vishay Semiconductors

Hyperfast Rectifier, 15 A FRED Pt[®] G5



LINKS TO ADDITIONAL RESOURCES



ion Models

PRIMARY CHARACTERISTICS								
I _{F(AV)}	15 A							
V _R	1200 V							
V _F at I _F at 125 °C	2.1 V							
t _{rr}	29 ns							
T _J max.	175 °C							
Package	D ² PAK 2L (TO-263AB 2L)							
Circuit configuration	Single							

FEATURES

- Minimum creepage and clearance distances are 5.2 mm and 5.4 mm respectively
- Hyperfast and optimized Q_{rr}
- Best in class forward voltage drop and switching
 HALOGEN
 FREE
 losses trade off
- Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- AEC-Q101 qualified meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for high frequency converters, both soft switched / resonant. Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

MECHANICAL DATA

Case: D²PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V _{RRM}		1200	V						
Average rectified forward current	I _{F(AV)}	T _C = 98 °C, D = 0.50	15							
Repetitive peak forward current	I _{FRM}	T _C = 98 °C, D = 0.50, f = 20 kHz	30	A						
Non-repetitive peak surge current	I _{FSM}	T_{C} = 45 °C, t_{p} = 10 ms, sine wave	110							
Operating junction and storage temperature	T _J , T _{Stg}		-55 to +175	°C						

ELECTRICAL SPECIFICATIONS ($T_J = 25 \ ^{\circ}C$ unless otherwise specified)										
PARAMETER	MIN.	TYP.	MAX.	UNITS						
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	1200	-	-					
Forward voltage		I _F = 15 A	-	2.5	3.3	V				
	V _F	I _F = 15 A, T _J = 125 °C	-	2.1	-					
Reverse leakage current	1	$V_{R} = V_{R}$ rated	-	-	50					
Reverse leakage current	IR	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA				
Junction capacitance	CT	V _R = 200 V	-	10	-	pF				
Series inductance	L _S	Measured to lead 5 mm from package body	-	8	-	nH				

Revision: 31-Jul-2023

Document Number: 96812

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

1



COMPLIANT







www.vishay.com

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST	CONDITIONS	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1.0 \text{ A}, dI_F/c$	$t = 100 \text{ A/}\mu\text{s}, \text{V}_{\text{R}} = 30 \text{ V}$	-	29	-				
Reverse recovery time	t _{rr}	T _J = 25 °C		-	96	-	ns			
		T _J = 125 °C		-	137	-				
Peak recovery current	1	T _J = 25 °C	l _F = 10 A dl _F /dt = 600 A/µs	-	11.5	-	А			
Peak recovery current	I _{RRM}	T _J = 125 °C	$V_{R} = 400 V$	-	16	-				
Reverse recovery charge	0	T _J = 25 °C		-	375	-	nC			
neverse recovery charge	Q _{rr}	T _J = 125 °C		-	900	-				
Reverse recovery time	+	T _J = 25 °C		-	77.5	-	20			
nevelse recovery line	t _{rr}	T _J = 125 °C		-	106	-	ns			
Peak recovery current	1	T _J = 25 °C	l _F = 15 A dl _F /dt = 1000 A/µs	-	21	-	A nC			
Feak recovery current	I _{RRM}	T _J = 125 °C	$d_{F}/dt = 1000 \text{ A/}\mu\text{s}$ $V_{B} = 800 \text{ V}$	-	29	-				
	0	T _J = 25 °C		-	680	-				
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	1600	-	nc			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Thermal resistance, junction-to-case	R _{thJC}		-	-	1.7	°C/W				
Weight			-	2.0	-	g				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C				
Marking device		Case style D ² PAK 2L (TO-263AB 2L)		E5TX ²	1512SH					

Revision: 31-Jul-2023 2 Document Number: 96812 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



VS-E5TX1512S2LHM3

Vishay Semiconductors

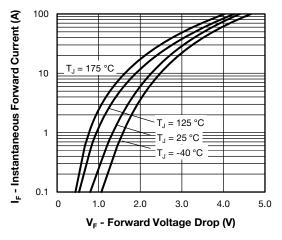


Fig. 1 - Forward Voltage Drop Characteristics

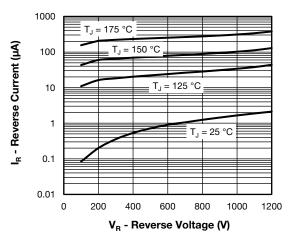


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

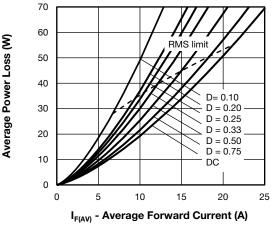


Fig. 5 - Forward Power Loss Characteristics

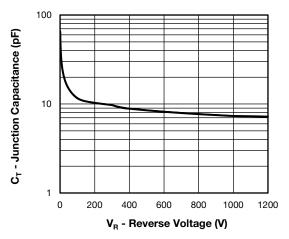


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

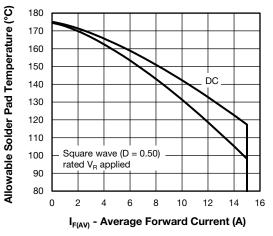


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

 Revision: 31-Jul-2023
 3
 Document Number: 96812

 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com
 THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

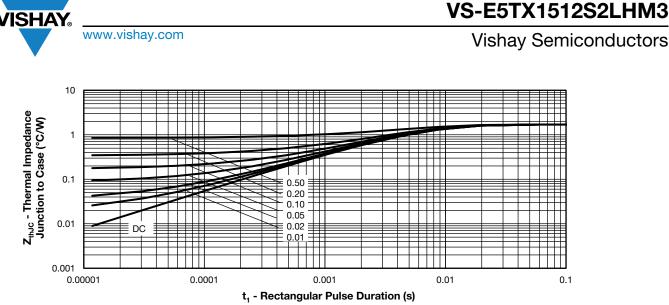


Fig. 6 - Transient Thermal Impedance, Junction to Case

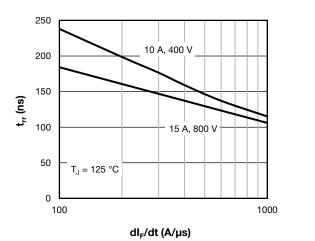


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

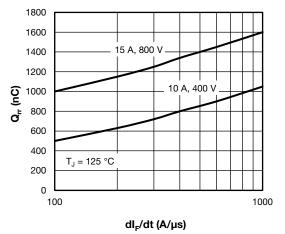


Fig. 8 - Typical Stored Charge vs. dl_F/dt

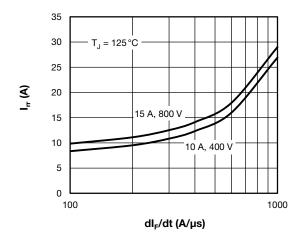


Fig. 9 - Typical Recovery Current vs. dI_F/dt



VS-E5TX1512S2LHM3

Vishay Semiconductors

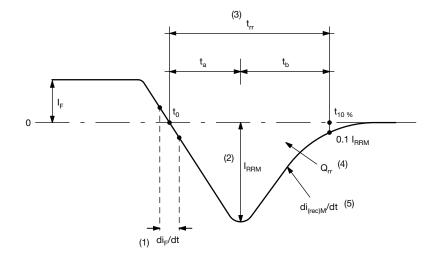


Fig. 10 - Reverse Recovery Waveform and Definitions

Notes

- ⁽¹⁾ di_F/dt rate of change of current through zero crossing
- ⁽²⁾ I_{RRM} peak reverse recovery current
- ⁽³⁾ t_{rr} reverse recovery time measured from t_0 , crossing point of negative going I_F, to point $t_{10\%}$, 0.1 I_{RRM} ⁽⁴⁾ Q_{rr} area under curve defined by t_0 and $t_{10\%}$

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t) dt$$

 $^{(5)}~di_{(rec)}M/dt$ - peak rate of change of current during t_b portion of t_{rr}

ORDERING INFORMATION TABLE

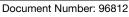
Device code	VS-	Е	5	т	x	15	12	S2	L	н	М3
		(2)	(3)	(4)	(5)	(6)	(7)	(8)	(9)	(10)	(11)
	1 -	\bigcirc	\bigcirc	niconduo	\bigcirc						
	2 - E = single diode										
	3 - 5 = FRED generation 5										
	4 -										
	5.	T = D ² PAK 2L (TO-263 2L) package - X = hyperfast recovery									
	6 -		51	ng (15 =							
	7.			ng (12 =	-	/)					
		- S2	= true 2	pin D ² F	PAK						
		 9 - None = tube (50 pieces) • L = tape and reel (left oriented, for D²PAK package) 									
	 If needed different orientation/packaging, please contact factory H = AEC-Q101 qualified 										
	<u>11</u>			ntal digit en-free,		complia	ant, and	termina	tion lea	d (Pb)-f	ree

ORDERING INFORMATION (Example)							
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION					
VS-E5TX1512S2LHM3	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS								
Dimensions	www.vishay.com/doc?96683							
Part marking information	www.vishay.com/doc?96693							
Packaging information	www.vishay.com/doc?95032							
SPICE Model	www.vishay.com/doc?97160							

VS-E5TX1512S2LHM3

Vishay Semiconductors

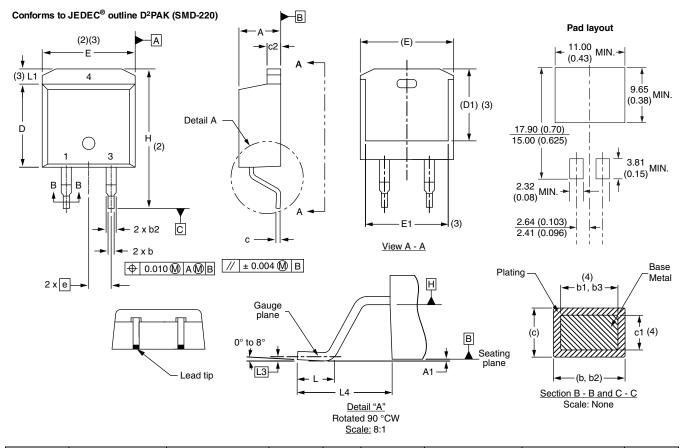


Vishay Semiconductors



D²PAK 2L (TO-263AB 2L)

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL		MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
с	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L3	0.25	BSC	0.010	BSC	
c2	1.14	1.65	0.045	0.065			L4	4.78	5.28	0.188	0.208	
D	8.51	9.65	0.335	0.380	2							

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
 (3) Thermal and contain antional within dimension E 1.1, D1 and E1.

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

(7) Outline conforms to JEDEC® outline TO-263AB

Revision: 14-Mar-2022

1

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.